

PART NUMBER

CH100, CH101, CH102, CH103



ISSUE 10

COMPONENT SPECIFICATION

Component Specification Transistor Optocouplers With Very Low Operating Temperatures

Features Applications	
 Total Ionizing Dose tested to 150 Krad(si) 	Space Equipment and Systems
 Displacement Damage to 1 MEV x 10¹² 	Military and High Reliability Systems
 Low Temperature Operation up to -150°C 	Medical Instruments
 4-pin Surface Mount Package 	Suitable for Hybrid Packaging
 Flexibility in Design for mounting styles 	 MOS/CMOS Applications
 High Current Transfer Ratio 	Data Transmission
 High Isolation Voltage up to 1,000Vdc 	 Power Supply
	Logic Interfacing

DESCRIPTION

The CH100 series is a single channel radiation hard optically coupled isolator. It is composed of an infrared emitting diode and a silicon phototransistor.

The CH100 has been designed and manufactured to meet the requirements of very low temperatures experienced in harsh environments encountered by space applications. These devices can be wire bonded within a hybrid application or mounted directly onto a PCB board offering the customer flexibility in their design. Package styles for this device include a 4-pin surface mount package, with solder dip option available.

Absolute maximum ratings, recommended operating conditions, electrical specifications and performance characteristics are identical for all units. Any exceptions, due to packaging variations and limitations, are as noted.









ISOCOM Limited is AS9100 certified for the design and manufacture of electronic and optoelectronic components.



STANDARDS

The following specifications have been included in the manufacturing of this product:

Aerospace Compliance Standards

AS9100D / ISO 9001:2015 – Design & Manufacture of Electronic and Optoelectronic Components (Ref GB15/92780)

Military Compliance Specifications

MIL-PRF-38534 – General Specification for Hybrid Microcircuits
MIL-PRF-19500 – General Specification for Discrete Semiconductor Devices

Military compliance standards

MIL-STD-202 – Test Method Standard Electronic and Electrical Component Parts MIL-STD-883 – Test Method Standard Microcircuits MIL-STD-750 – Test Method Standard for Semiconductor Devices

SCREENING INFORMATION

Our products can be screened to MIL-PRF-38534, applying test methods from MIL-STD-883; MIL-PRF-19500, applying test methods of MIL-STD-750; or a combination thereof. Please contact us for more information relating to the applicable screening processes.

AMENDMENT RECORD

Issue No.	Date	Description	
1	December 2013	First issue.	
2	May 2018	Updated 'Standards' section.	
3	October 2018	Outline drawing amended. Added front cover.	
4	May 2019	Updated 'Standards' section, Screening, Group Test and Hermetically sealed information removed.	
5	August 2019	Updated electrical characteristics.	
6	September 2020	Updated Quality Management Logos and removed IECQ Logos	
7	May 2022	Added Radiation Testing and Electrical Testing Diagrams	
8	June 2022	Updated Electrical Characteristic Graphs and Added Screening Flow	
9	June 2023	Updated Marking Image	
10	August 2023	Added pin configuration, updated screening and updated circuit drawings	

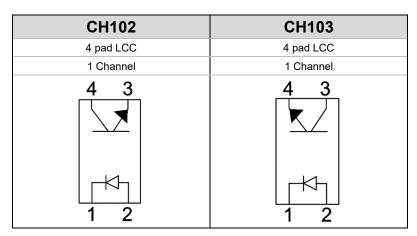


SELECTION GUIDE PACKAGE STYLES AND CONFIGURATION OPTIONS

ISOCOM Part Number and Options			
Package	4-pin Surface Mount		
Lead Style	-		
Channels	1		
Common Channel Wiring	-		
Commercial	CH100 CH101 CH102 CH103		
Defense Screen Level	CH100/L2 CH101/L2 CH102/L2 CH103/L2		
Space Screen Level	CH100/L2S CH101/L2S CH102/L2S CH103/L2S		
Standard Finish	Gold Plating		
Solder Dipped	Option 20		

FUNCTIONAL DIAGRAMS

CH100	CH101
4 pad LCC	4 pad LCC
1 Channel	1 Channel
4 3 × / 1 2	4 3 1 2





PIN OUT

011400	Pin number	function
CH100	1	Anode
	2	Cathode
	3	Collector
	4	Emitter

011400	Pin number	function
CH102	1	Cathode
	2	Anode
	3	Emitter
	4	Collector

011404	Pin number	function
CH101	1	Anode
	2	Cathode
	3	Emitter
	4	Collector

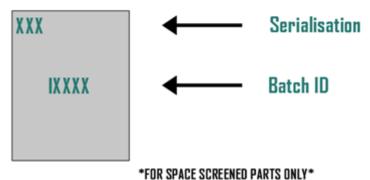
CH103	Pin number	function
CH103	1	Cathode
	2	Anode
	3	Collector
	4	Emitter

DEVICE MARKING





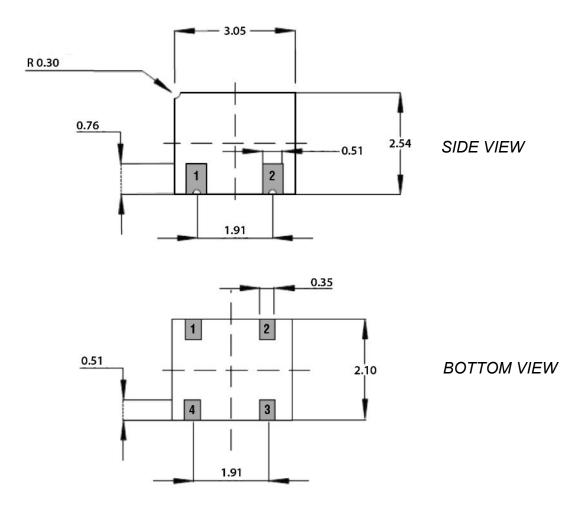
BACK OF DEVICE



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OUTLINE DRAWINGS





ABSOLUTE MAXIMUM RATINGS

T_A = 25°C U.O.S.

Storage Temperature	-65°C to +150	-65°C to +150°C		
Operating Temperature	-55°C to +125	-55°C to +125°C		
Lead Soldering Temperature	260°C 1.6mm	from case for 10 seconds		
Input-to-Output Isolation Voltage	û1,500 V _{DC}			
Input Diode				
Forward DC Current	50mA			
Reverse DC Voltage	7V			
Peak forward Current	1.5A	≤ 10µs		
Power Dissipation	150mW			
Output Transistor				
Collector-Emitter Voltage	70V			
Emitter-Collector Voltage	7V			
Collector-Base Voltage	70V	≤ 10µs		
Collector Current	100mA	t =1ms		
Power Dissipation	150mW	Derate linearly above 100°C at 1.4W/°C		
Coupled Device	'	·		
Power Dissipation	360mW			
Soldering Temperature, Soldering Iron	260.5°C	This part shall not be re-soldered until 3 minutes have elapsed.		
Soldering Temperature, Vapour Phase	220.40°C	This part shall not be re-soldered until 3 minutes have elapsed.		
ESD Classification	Class 2	Class 2 with minimum critical path voltage of 4,000 to 15,999V. MIL-STD-883		



ELECTRICAL CHARACTERISTICS

 $T_A = 25$ °C U.O.S.

Parameter	Symbol	Test Conditions	Min	Туре	Max	Units
Input Diode Electrical Characteristics						
		I _F = 10mA	1.3	_	1.8	V
Forward Voltage	V _F	I _F = 10mA -55°C	1.3	_	1.8	V
		I _F = 10mA +125°C	1.1	_	1.8	V
Reverse Current	I _R	V _R = 2.0V	_	_	100	μA
Output Detector Ele	ctrical Ch	aracteristics				
Collector-Emitter Breakdown Voltage	V(BR) _{CEO}	I _{CE} = 1mA	70	100	-	٧
Emitter-Collector Breakdown Voltage	V(BR) _{ECO}	I _{EC} = 0.1mA	7	9	-	V
		V _{CE} = 20V, I _F = 0A	_	7	100	μA
Collector–Emitter Leakage Current	I _{CEO}	V _{CE} = 20V, I _F = 0A, -55°C	_	_	100	μA
		V _{CE} = 20V, I _F = 0A, +125°C	-	10	150	μA
Coupled Electrical C	haracteri	stics				
DC Current Transfer Ratio		I _F = 1.0mA, V _{CE} = 5V	100	_	_	%
DC Current Transfer Ratio	IC/IF	I _F = 10.0mA, V _{CE} = 5V (Note 1)	150	_	_	%
Collector-Emitter Saturation Voltage	V _{CE} (Sat)	I _C = 10.0mA I _F = 20mA	_	_	0.3	V
Isolation Voltage	V in-out	T = 5s (Note 2)	_	1000	_	V_{dc}
Input to Output Resistance	R in-out	V _{IO} = 500V (Note 2)	_	10 ⁵	_	Ω
Rise Time	t _r	$R_L = 100\Omega$, $V_{CC} = 10V$, $I_F = 10mA$	_	7	20.0	μs
Fall Time	t _f	$R_L = 100\Omega$, $V_{CC} = 10V$, $I_F = 10mA$	_	7	20.0	μs

Notes

- 1. Sample and hold pulse shall not be longer than 0.1 seconds. Duty cycle shall be 10%.
- 2. Measurements with inputs shorted together and outputs shorted together.

ELECTRICAL MEASUREMENTS DURING AND ON COMPLETION OF RADIATION TESTING

Parameter	Symbol	Test Conditions	Min	Max	Units
Input Diode Forward Voltage	V_{F}	I _F = 10Ma	1.3	1.8	V
Input Diode Reverse Current	I _R	V _R = 2.0V	-	100	μΑ
Photo Transistor Collector-Emitter Dark Current	ICEO	VCE = 20v, IF = 0A	-	100	μΑ
Coupled Current Transfer Datie	10	I _F = 1.0Ma, V _{CE} = 5V	100	_	%
Coupled Current Transfer Ratio	IC	I _F = 10.0Ma, V _{CE} = 5V (note 1)	150	-	%
Collector-Emitter Saturation Voltage	V _{CE} (Sat)	I _C = 10.0Ma, I _F = 20Ma	_	0.3	V

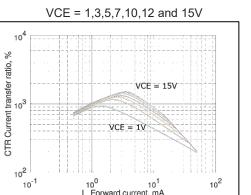
Notes

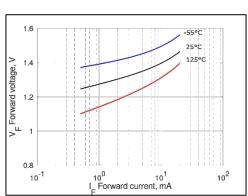
- 1. Sample and hold pulse shall be no longer than 0.1 seconds. Duty cycle shall be 10%.
- 2. Please note that if you require any parameters to be controlled to meet your design needs such as CTR, V_F, I_{CEO}, VCE(SAT), please contact ISOCOM Limited customer service team. We also offer a selection of screening procedures that will match your needs.

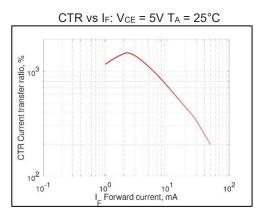


ELECTRICAL CHARACTERISTICS

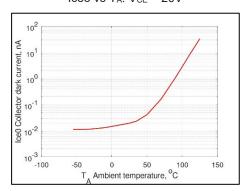
Typical Graphs - Contact Office for more information



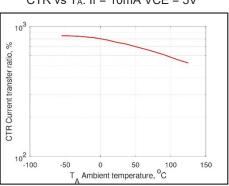




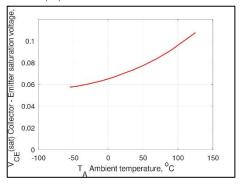
Iceo vs T_A: V_{CE} = 20V



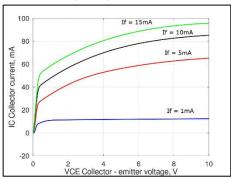
CTR vs T_A: If = 10mA VCE = 5V



V_{CE(sat)} vs T_A: If = 20mA IC = 10mA

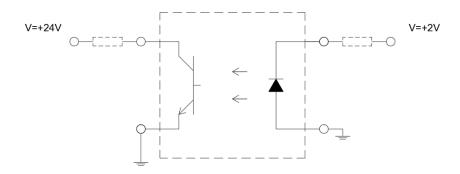


I_C vs V_{CE}: T_A = 25°C

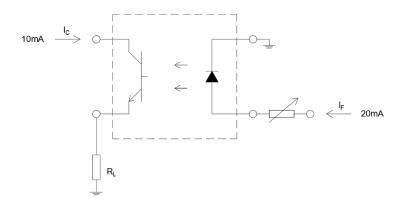




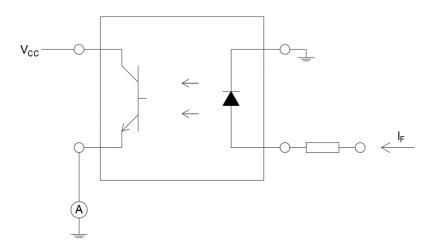
HTRB TEST CIRCUIT



ELECTRICAL CIRCUIT FOR BURN-IN AND OPERATING LIFE TESTS

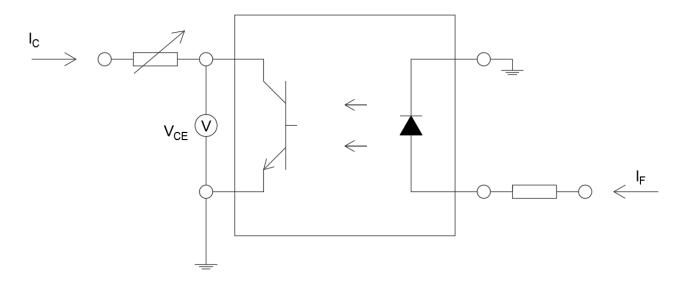


ELECTRICAL MEASUREMENT OF COLLECTOR CURRENT

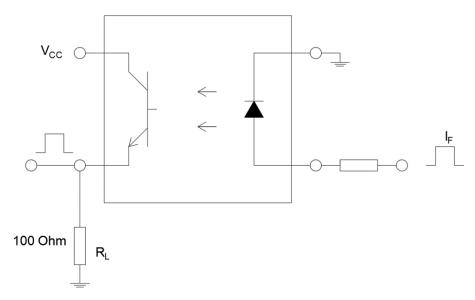




ELECTRICAL MEASUREMENT OF COLLECTOR EMITTER SATURATION VOLTAGE

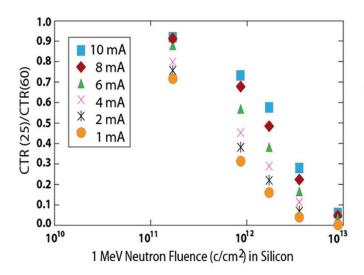


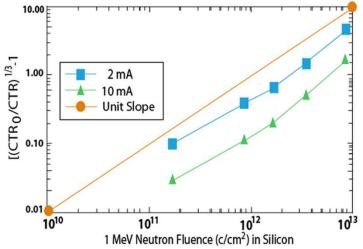
ELECTRICAL MEASUREMENT OF A.C PARAMETERS





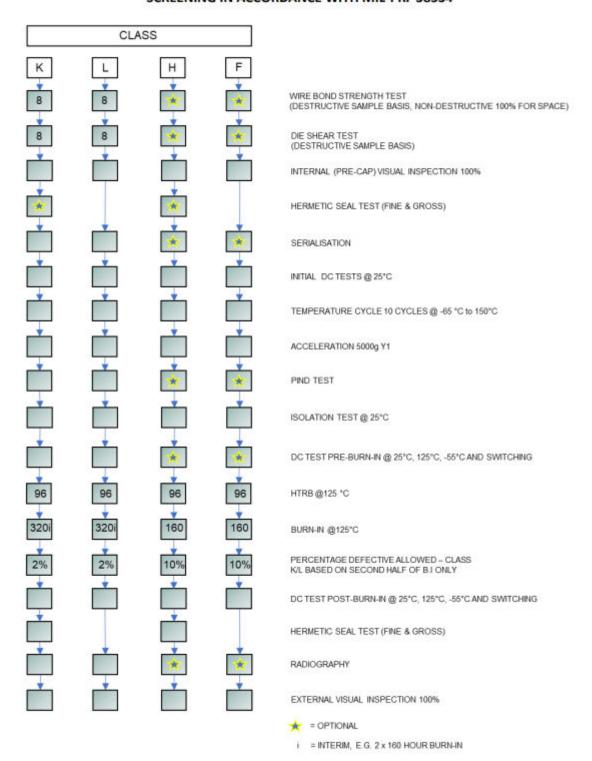
RADIATION TESTING







SCREENING IN ACCORDANCE WITH MIL-PRF 38534



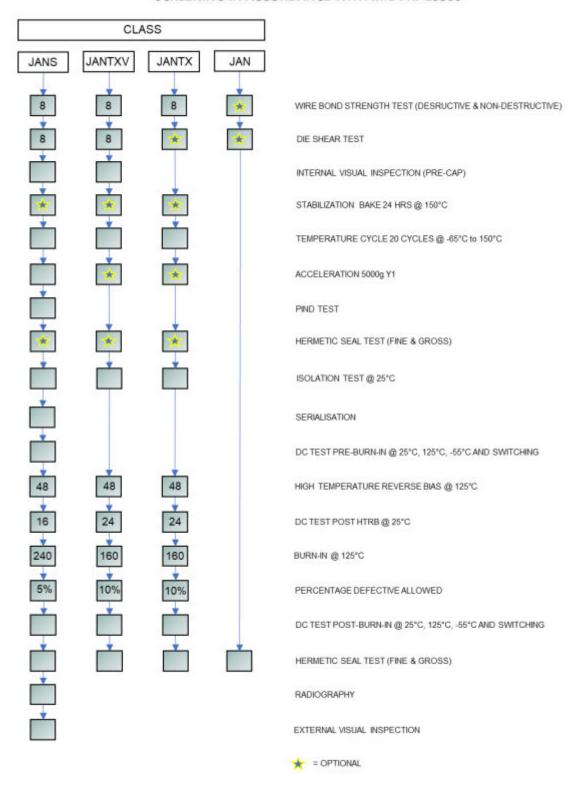


The following screening flow includes the electrical tests between each screening step, the referenced test method from MIL-STD 883 and the sample basis for Class K/L and H/F quality levels.

Operation No.	Towns and the second	MIL-STD 883 TEST METHOD	Class		
Operation No.	Operation	MIL-STU 883 TEST METHOD	H/F (L2)	K/L (L28)	
1	Wire bond strength (ND)	(883) 2023	Optional	100%	
2	Wire bond strength (D)	(883) 2011	Optional	8 devices	
3	Die Shear	(883) 2019	Optional	8 devices	
4	Internal Visual	(883) 2017	100%	100%	
5	Fine leak, Helium bomb, Leak detector	(883) 1014, Con A1	Optional	Optional	
6	Gross leak, Liquid bomb, -Bubble chamber	(883) 1014, Con C1	Optional	Optional	
7	Senalisation of devices		Optional	100%	
8	Electrical Test 25°C		100%	100%	
9	Temp cycle @ -65°C to 150°C	(883) 1010, Con C, 10 cycles	100%	100%	
10	Electrical Test 25°C		100%	100%	
11	Constant acceleration	(883) 2001, 3000g, Y1	100%	100%	
12	Electrical Test 25°C		100%	100%	
13	PIND	(883) 2020, Con A	Optional	100%	
14	Electrical Test 25°C		100%	100%	
15	Isolation 100% @ 25°C	(MIL-STD 202) 301	100%	100%	
16	Electrical Test 25°C		100%	100%	
17	Electrical Test 125°C		Optional	100%	
18	Electrical Test -55°C		Optional	100%	
19	Switching time 100% @ 25°C		Optional	100%	
20	HTRB @ 125°C - 96 hrs	(883) 1015, con A	100%	100%	
21	Electrical Test 25°C		100%	100%	
22	Burn in @ 125°C	(883) 1015, con B	100% 160 hours	100% 160 hrs	
23	Electrical Test 25°C		100%	100%	
24	Burn in @ 125°C	(883) 1015, con B	N/A	100% 160 hrs	
25	Percentage defective allowable	Pre/post Burn-in electrical and delta at 25°C only	Max. 10%	Max. 2%	
26	Electrical Test 25°C	Group A - 9G1	100%	100%	
27	Electrical Test 125°C	Group A - SG2	100%	100%	
28	Electrical Test -55°C	Group A - 9G3	100%	100%	
29	Switching time 100% @ 25°C	Group A - SG9	100%	100%	
30	Fine leak, Helium bomb, Leak detector	(883) 1014, Con A1	100%	100%	
31	Gross leak, Liquid bomb, -Bubble chamber	(883) 1014, Con C1	100%	100%	
32	Radiography	(883) 2012	Optional	100%	
33	External Visual	(883) 2009	100%	100%	



SCREENING IN ACCORDANCE WITH MIL-PRF 19500





The following screening flow includes the electrical tests between each screening step, the referenced test method from MIL-STD 750 and the sample basis for Class JANTX, JANTXV and JANS quality levels.

Operation		. MIL-PRF 19500	Class		
No.	Operation	MIL-PRF 19909	JANTX (L2)	JANTXV (L2)	JANS (L2S)
1	Wire bond strength (ND)	(883) 2023	100%	100%	100%
2	Wire bond strength (D)	e bond strength (D) (750) 2037, Con D		4 devices	8 devices
3	Die Shear	Die Shear (750) 2017		4 devices	8 devices
4	Internal Visual (750) 2072		Optional	100%	100%
5	Stabilization Bake		Optional	Optional	Optional
6	Electrical Test @ 25°C		100%	100%	100%
	Temp cycle (20 cycles @ -65°C to 150°C)	(750) 1051, Con F	100%	100%	100%
8	Electrical Test @ 25°C		100%	100%	100%
9	Constant acceleration	(750) 2006, 5000g, Y1	Optional	Optional	100%
10	Electrical Test @ 25°C		100%	100%	100%
11	P.I.N.D	(750) 2052, Con A	N/A	N/A	100%
12	Electrical Test @ 25°C		N/A	N/A	100%
13	Fine leak, Helium bomb, -Leak detector (750) 1071 Con H1		Optional	Optional	Optional
14	Gross leak, Liquid bomb, Bubble chamber	(750) 1071, Con C	Optional	Optional	Optional
15	Serialisation of devices		N/A	N/A	100%
16	Isolation 100% @ 25°C	(MIL-STD 202) 301	100%	100%	100%
17	Electrical Test @ 25°C		100%	100%	100%
18	Electrical Test @ 125°C		100%	100%	100%
19	Electrical Test @ -55°C		100%	100%	100%
20	Switching time @ 25°C		100%	100%	100%
21	HTRB (125°C)	(750) 1039, Con A (80% VDS)	100% (48 hrs)	100% (48 hrs)	100% (48 hrs)
22	Electrical Test @ 25°C		100% (24 hrs)	100% (24 hrs)	100% (16 hrs)
23	Burn-in (125°C)	(750) 1039, Con B (80% VDS)	100% (160 hrs)	100% (160 hrs)	100% (240 hrs)
24	Percentage defective allowable	Pre/post Burn-in electrical and delta at 25°C only	100% @ 10% PDA	100% @ 10% PDA	100% @ 5% PDA
25	Electrical Test @ 25°C		100% (Group A, BG 2)	100% (Group A, SG 2)	100% (Group A, SG 2
26	Electrical Test @ 125°C		100% (Group A, SG 3)	100% (Group A, SG 3)	100% (Group A, SG 3
27	Electrical Test @ -55°C		100% (Group A, SG 3)	100% (Group A, SG 3)	100% (Group A, SG)
28	Switching time @ 25°C		100% (Group A, SG4)	100% (Group A, SG4)	100% (Group A, SG4
29	Fine leak, Helium bomb, -Leak detector	(750) 1071 Con H1	100%	100%	100%
30	Gross leak, Liquid bomb, Bubble chamber	(750) 1071, Con C	100%	100%	100%
31	Radiography	(750) 2076	N/A	N/A	100%
32	External Visual	(750) 2071	N/A	N/A	100%



MIL-PRF 19500 TYPICAL QCI TESTING PROCESS FLOW

Group	Sub	Parameters	Quantity (accept number)			
	Group		TM	JANS	JANTX, JANTXV	
A (CI)	1	Visual and mechanical inspection	750-2071	2.0000000	100%	
	2	Static tests at +25°C	Datasheet	100%		
	3	Static tests at min and max, rated operating temp.	Datasheet	100%		
	4	Dynamic test at +25°C	Datasheet			
		(JANS)		Large LOT (accept)	Small LOT (accept)	
	1	Physical dimension	750-2066	22 (0)	8 (0)	
	2	Solderability	750-2026	15 leads (0)	6 leads (0)	
		Temperature cycling (100 cycles)	750-1051	22 (0)	6 (0)	
		Hermetic seal (fine and gross leak)	750-1071			
		Electrical measurements	GRP-A- SG2	22 (0)		
p (pn	3	Decap internal visual	750-2075	6 (0)	6 (0)	
B (PI)		Bond strength	750-2037	22 wires (0) or 11 (0)	12 wires (0) or 6 (0)	
		SEM	750-2077	11 (0)	6 (0)	
	Ī	Die shear	750-2017	11 (0)	6 (0)	
		Intermittent operation life (2000 cycles)	750-1037		12 (0)	
	4	Electrical measurements	GRP-A- SG2	22 (0)		
*		(JANTXV, JANTX)		Large LOT (accept)	Small LOT (accept)	
-	1	Solderability	750-2026	15 leads (0)	4 leads (0)	
		Temperature cycling (45 cycles incl. screening)	750-1051	22 (0)	6 (0)	
	2	Hermetic Seal (fine and gross leak)	750-1071			
B (PI)	<u> </u>	Electrical measurements	GRP-A-	22 (0)		
			SG2			
		Steady state op. life (340 Hrs) or intermittent op. life (2000 cycles)	750-1026			
			or 750-	46 (0)	12 (0)	
	3		1037 GRP-A-	45 (0)		
		Electrical measurements	SG2			
	4	Decap internal visual	750-2075	1 (0)	1 (0)	



MIL-PRF 19500 TYPICAL QCI TESTING PROCESS FLOW

Group	Sub Group	Parameters	ТМ	Sample plan	Small LOT (accept)
	1	Physical dimensions (Not Req. JANS)	750-2066	15 (0)	6 (0)
	2	Thermal shock (25 cycles, con B)	750-1056	22 (0)	6 (0)
		Temperature cycling (45 cycles incl. screening)	750-1051		
		Terminal strength	750-2036		
		Hermetic seal (fine and gross leak)	750-1071		
		Electrical measurements	GRP-A-		
			SG2		
C (PI)	3	Constant acceleration (5000g, Y1 only)	750-2006	22 (0)	6 (0)
		Electrical measurements	GRP-A-		
			SG2		
	6	Steady state op. life (1000 Hrs) or intermittent op. life (6000 cycles)	750-1026		
			or 750-		
			1037	22 (0)	12 (0)
		Electrical measurements	GRP-A-		
			SG2		
	7	Internal Gas Analysis - Moisture 10,000 ppmv limit	750-1018	3 (0)	3 (0)



MIL-PRF 38534 TYPICAL QCI TESTING PROCESS FLOW

Group	Sub Group	Daramactore		CONTROL OF THE PARTY	cept number)
		Parameters	TM	К	н
A (CI)	1	Static tests at +25°C	Datasheet	100%	100%
	2	Static tests at max. rated operating temp.	Datasheet	100%	100%
A (CI)	3	Static tests at min. rated operating temp.	Datasheet	100%	100%
	9	Switching tests at +25°C	Datasheet	100%	100%
	1	Physical dimension	883-2016	2 (0)	2 (0)
	4	Internal visual and mechanical	883-2014	1 (0)	1 (0)
500	5	Bond strength: Ultrasonic (on hotplate)	883-2011	2 (0)	2 (0)
B (PI)	6	Die shear strength	883-2019	2 (0)	2 (0)
	7	Solderability	883-2003	1 (0)	1 (0)
	8	Seal: a. Fine, b. Gross	883-1014	N/A	15 (0)
	ĩ	External visual	883-2009	5 (0)	5 (0)
		Temperature Cycling	883-1010	5 (0)	5 (0)
		Constant acceleration	883-2001	X	5 (0)
		Seal (fine and gross)	883-1014	5 (0)	5 (0)
		PIND	883-2020	5 (0)	5 (0)
C (PI)		Visual examination	883-1010	5 (0)	5 (0)
		End-point electrical	GRP-A	5 (0)	5 (0)
	2	Steady-state life test	883-1005	22 (0) or 5 (0)	22 (0) or 5 (0)
		End-point electrical	GRP-A	22 (0) or 5 (0)	22 (0) or 5 (0)
	3	Internal gas analysis Moisture 10,000 ppmv limit	883-1018	3 (0) or 5 (1)	3 (0) or 5 (1)
		Thermal shock	883-1011	5 (0)	5 (0)
	1	Stabilization bake	883-1011	5 (0)	5 (0) 5 (0)
D (PI)			883-2004	5 (0)	
		Lead integrity Seal: a. Fine, b. Gross	883-2004 883-1014	1 (0) 5 (0)	1 (0) 5 (0)



Summary of key differences between MIL-PRF 19500 and MIL-PRF 38534 for space level testing:

	MIL-PRF 19500 - JANS	MIL-PRF 38534 – Class K		
No. of Operation	31	33		
(Screening) Steps	· ·	55		
Optional				
Hermeticity	Occurs post P.I.N.D	Occurs post Internal Visual		
Testing				
Temp cycle – No.	20	10		
of Temp Cycles				
Acceleration -	5000g	3000g		
Amount of g force	-			
HTRB – No. of	48	96		
hours		33		
Burn-in – No. of	240 hrs in one successive burn-in	320 hrs (2 x 160 hrs with interim electrical)		
hours	2 is the sit one sales solve built in	SES INS LEX 135 INS WAI INCOME GROWING		
PDA post burn-in	5% after 240 hrs burn-in	2% after second 160 hrs burn-in		



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